

13

30. The process as claimed in claim **17**, further comprising:
coating the connection structures with a structured covering layer before the coating with the copy-protect layer;
thinning the copy-protect layer at least until the structured covering layer has been uncovered; and
removing the structured covering layer to uncover the connection structure regions.

31. The process as claimed in claim **18**, wherein the substrate comprises a semiconductor layer of silicon and the copy-protect layer comprises silicon.

14

32. The process as claimed in claim **28**, further comprising removing the plastics layer from the second side.

33. The process as claimed in claim **28**, further comprising filling the etching pits with conductive material.

34. The process as claimed in claim **28**, further comprising applying a ball grid array to the first side of the substrate on the connection structure regions.

35. The process as claimed in claim **30**, wherein at least sections of the structured covering layer and at least sections of the copy-protect layer are removed by a lift-off technique.

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